

TQELSG215V0

TheTQELSG215V0 provides a typical line to line capacitance of 0.1pF and low insertion loss up to 10GHz providing greater signal integrity making it ideally suited for USB 3.0 applications, such as Digital TVS, DVD players, Computing, set-top boxes and MDDI applications in mobile computing devices.

It has been specifically designed to protect sensitive components which are connected to high-speed data and transmission lines from over voltage caused by ESD(electrostatic discharge), CDE (Cable Discharge Events),and EFT (electrical fast transients).

Features

- Protects four I/O lines and one Vcc line
- Low capacitance
- Working voltages : 5V
- Low leakage current
- Low capacitance (<0.8pF) for high-speed interfaces
- No insertion loss to 10.0GHz
- Response Time is < 1 ns
- Meets MSL 1 Requirements
- Solid-state silicon avalanche technology
- ROHS compliant
- TECH CHIP technology

Main applications

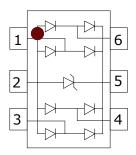
- Digital Visual Interface (DVI)
- 10/100/1000 Ethernet
- USB 1.1/2.0/3.0/OTG
- IEEE 1394 Firewire Ports
- Projection TV Monitors and Flat Panel Displays
- Notebook Computers
- Set Top Box
- Projection TV

Protection solution to meet

- IEC61000-4-2 (ESD) ±20kV (air), ±20kV (contact)
- IEC61000-4-4 (EFT) 40A (5/50ns)
- IEC61000-4-5 (Lightning) 4A (8/20µs)

Ordering Information

Device	Marking	Qty per Reel	Reel Size
TQELSG215V0	F54	3000	7 Inch



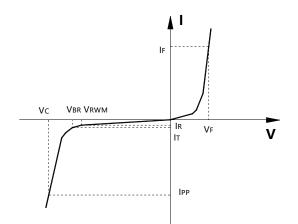
SOT-363

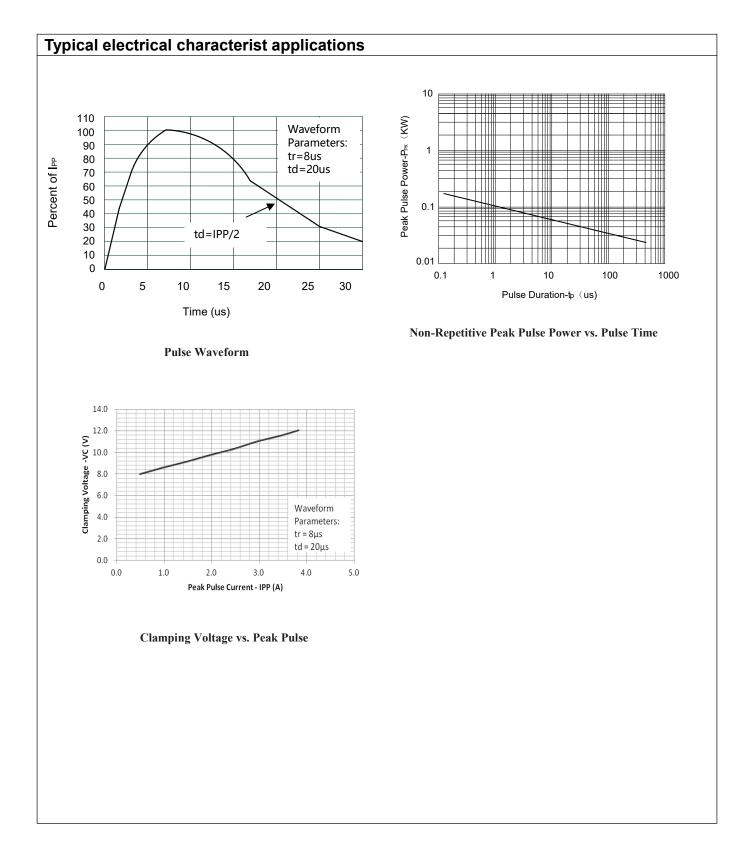
Maximum ratings (Temp=25°C Unless Otherwise Specified)				
Parameter	Symbol	Value	Unit	
Peak Pulse Power (tp=8/20µs waveform)	Ррр	40	Watts	
Peak Pulse Current(tp=8/20µs waveform)	IPP	4	А	
ESD Rating per IEC61000-4-2: Contact Air		20 20	KV	
Lead Soldering Temperature	Τι	260 (10 sec.)	°C	
Operating Temperature Range	TJ	-55 ~ 150	°C	
Storage Temperature Range	Тѕтс	-55 ~ 150	°C	

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
VRWM	Reverse Working Voltage	Any I/O to Ground			5.0	V
Vbr	Reverse Breakdown Voltage	IT = 1mA, Any I/O to Ground	6.0			V
lr	Reverse Leakage Current	V _{RWM} = 5V, Any I/O to Ground			1	μA
VF	Diode Forward Voltage	IF = 15mA		0.94	1.2	V
		I _{PP} = 1A, tp =8/20μs, any I/O pin to Ground		7.8	9.6	V
VC	Vc Clamping Voltage	I _{PP} = 4A, tp =8/20μs, any I/O pin to Ground		12	15.0	V
I _{PP}	Peak Pulse Current	tp =8/20µs			4	А
CJ ,	Junction Capacitance	V _R = 0V, f = 1MHz, between I/O pins		0.1	0.3	pF
		VR = 0V, f = 1MHz, any I/O pin to Ground		0.45	0.8	pF

Junction capacitance is measured in VR=0V,F=1MHz

Symbol	Parameter	
Vrwm	Working Peak Reverse Voltage	
Vbr	Breakdown Voltage @ IT	
V _C	Clamping Voltage @ IPP	
I _T	Test Current	
Irm	Leakage current at VRWM	
Ipp	Peak pulse current	
Co	Off-state Capacitance	
CJ	Junction Capacitance	

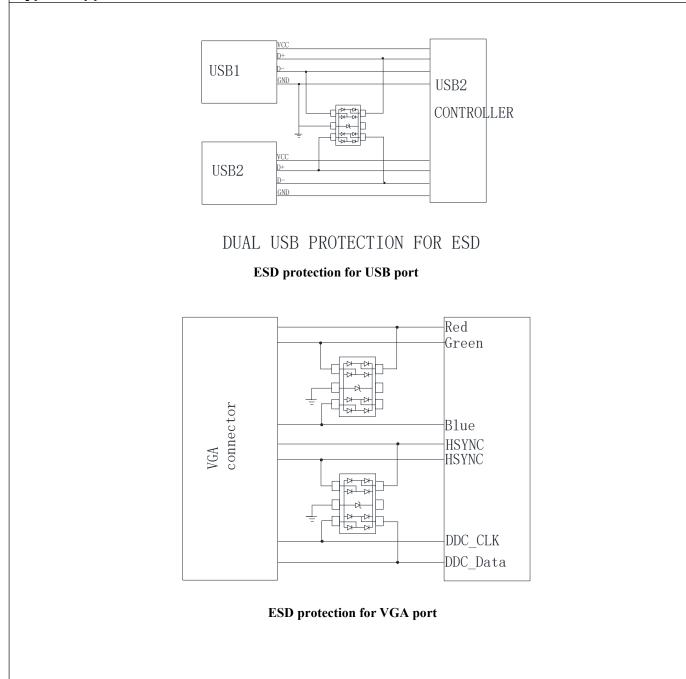






TQELSG215V0

Typical applications



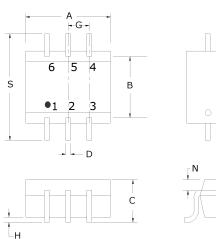


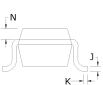
Package Information

SOT363

Mechanical Data

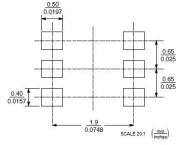
- Case: SOT363
- Case Material: Molded Plastic. UL Flammability





Dim	Millimeters		
וווים	MIN	МАХ	
Α	2.00	2.20	
В	1.15	1.35	
С	0.90	1.10	
D	0.15	0.35	
G	0.65	0.65BSC	
Н		0.10	
J	0.08	0.15	
К	0.15	0.35	
N	0.20REF		
S	2.15	2.45	

Recommended Pad outline





TQELSG215V0

DISCLAIMER

TECH CHIP RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. TECH CHIP DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICIENCE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

THE GRAPHS PROVIDED IN THIS DOCUMENT ARE STATISTICAL SUMMARIES BASED ON A LIMITED NUMBER OF SAMPLES AND ARE PROVIDED FOR INFORMATIONAL PURPOSE ONLY. THE PERFORMANCE CHARACTERISTICS LISTED IN THEM ARE NOT TESTED OR GUARANTEED. IN SOME GRAPHS, THE DATA PRESENTED MAY BE OUTSIDE THE SPECIFIED OPERATING RANGE (E.G., OUTSIDE SPECIFIED POWER SUPPLY RANGE) AND THEREFORE OUTSIDE THE WARRANTED RANGE.